YJQ200P10AJ

P-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	-100V
I_D	-8A
$R_{DS(ON)}$(at V_{GS}=-10V)	200m
$R_{DS(ON)}$(at V_{GS}=-4.5V)	235m
100% EAS Tested	
100% V_{DS} Tested	

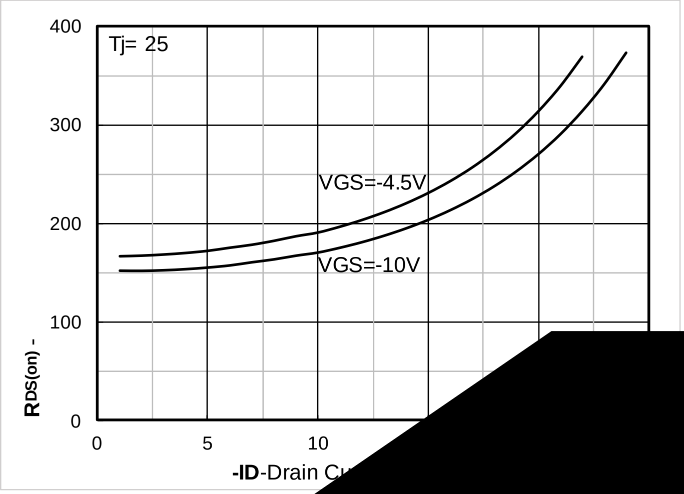
General Description

Electrical Characteristics (T$_J$=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units

s

Typical Electrical 50.57WBT/F5 10.56Tf1 0 0 1 2.94 20.4Tm0 g0 G[2)]T3c[ica



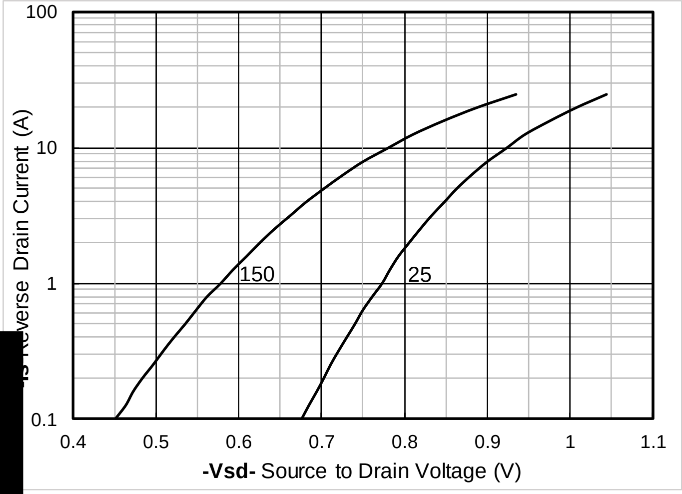


Figure 7. D

Figure

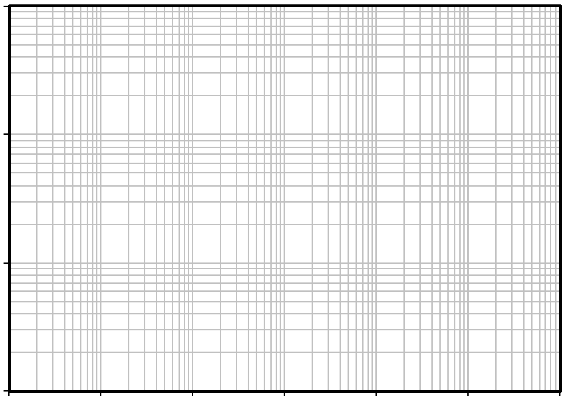


Figure 13. Maximum Transient Thermal Impedance

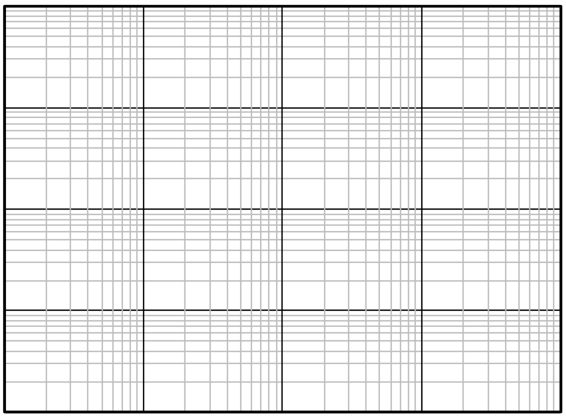
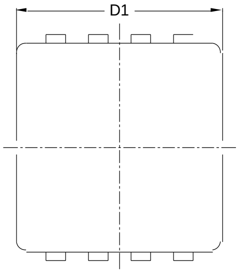
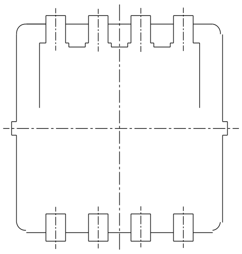


Figure 14. Safe Operation Area

PDFN3333-8L-B-0.75MM Package information





UNIT mm

NOTE:
1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

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